INIKC Power Module for Battery Pack



# **Features**

- Input Voltage up to 12V
- MOSFET Turn on Resistor RSS(ON) =2.2mohm(typ)@Vgs=3.8V
- Drain to Drain MOSFET Module
- With ESD Protection
- Continuous Current=20A
- Green Product (RoHS, Lead-Free, • Halogen-Free Compliant)

# **Applications**

## **General Description**

The GS95B9CS-R drain to drain connected MOSFET module provides an integrated solution with small dimension for battery pack of Mobile phone and electronic bracelet application.

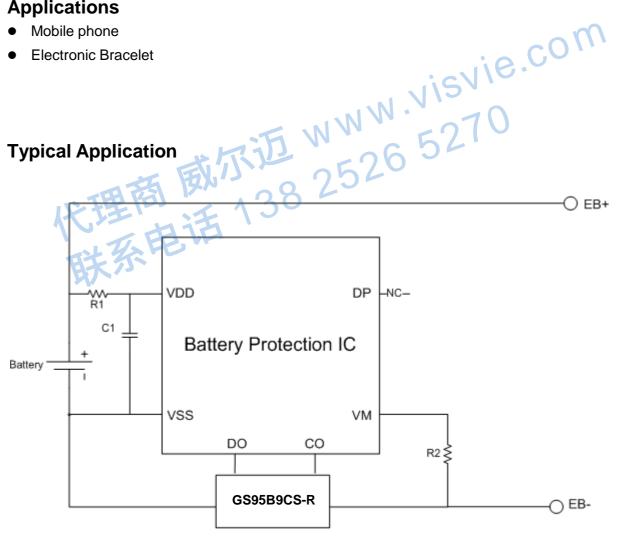
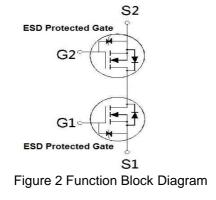


Figure 1 Application of GS95B9CS-R used in battery pack



# Function Block Diagram



# **Pin Configuration**

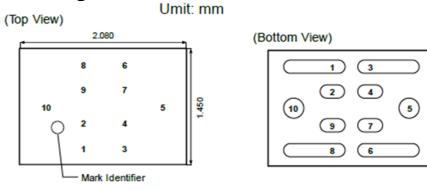


Figure 3 WLCSP 2.08x1.45

# **Pin Descriptions**

No.	Name	I/O type	Description
1	S1	I/O	Source1
2	S1	I/O	Source1
3	S1	I/O	Source1
4	S1	I/O	Source1
5	G1	I	Gate1
6	S2	I/O	Source2
7	S2	I/O	Source2
8	S2	I/O	Source2
9	S2	I/O	Source2
10	G2	Ι	Gate2



# Absolute Maximum Ratings (T<sub>A</sub>=25°C Unless Otherwise Noted)

PARAMETER / TEST CONDITIONS	SYMBOL	LIMITS	UNITS
Source-Source Voltage	V <sub>SSS</sub>	12	V
Gate-Source Voltage	V <sub>GSS</sub>	±8	V
Continuous Source Current	I <sub>S</sub>	20	А
Pulsed Source Current <sup>1</sup>	I <sub>SP</sub>	140	А
Total Dissipation <sup>2</sup>	PT	1.5	W
Thermal Resistance <sup>2</sup>	$R_{ ext{ heta}JA}$	70	<sup>°</sup> C/W
Operating Junction & Storage Temperature Range	Tj & Tstg	-55~150	°C

 $^{1}$ PW $\leqslant$ 10µs, duty cycle $\leqslant$ 1%.

<sup>2</sup>When mounted on 1in<sup>2</sup> FR-4 board.

### **Electrical Characteristics (TJ=25°C Unless Otherwise Noted)**

	SYMBOL	TEST CONDITIONS	LIMITS			
PARAMETER			MIN	TYP	MAX	UNITS
		STATIC				
Source-Source Breakdown Voltage	V(BR)SSS	$V_{GS} = 0V, I_S = 1mA$	12			V
Gate Threshold Voltage	VGS(th)	$V_{SS} = 10V$ , $I_S = 1mA$	0.35	0.90	1.4	•
Gate-Source Leakage	IGSS	$V_{SS} = 0V, V_{GS} = \pm 8V$			±10	uA
Cale-Oburce Leakage		$V_{SS} = 0V, V_{GS} = \pm 5V$			±1	
Zero Gate Voltage	1	VSS = 12V , VGS = 0V			1	uA
Source Current	I <sub>SSS</sub>	V33 = 12V, V33 = 0V				
		$V_{GS} = 4.5V, I_S = 3A$	1.50	2.05	2.70	
Drain-Source On-State		$V_{GS} = 3.8V, I_S = 3A$	1.60	2.20	2.85	mΩ
Resistance <sup>1</sup>	RSS(ON)	$V_{GS} = 3.1V, I_S = 3A$	1.75	2.55	3.90	
		$V_{GS} = 2.5V, I_S = 3A$	2.00	3.30	6.60	





DYNAMIC						
Input Capacitance	C <sub>iss</sub>		TBD			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0V, V_{DS} = 12V, f = 1MHz$	TBD		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>		TBD			
Gate Resistance	R <sub>g</sub>	F=1MHz	400		Ω	
Total Gate Charge <sup>2</sup>	Qg	$V_{SS} = 12V , V_{GS} = 4.5V, I_S = 5A$	TBD		nC	
Turn-On Delay Time <sup>2</sup>	t <sub>d(on)</sub>		TBD			
Rise Time <sup>2</sup>	t <sub>r</sub>		TBD		nS	
Turn-Off Delay Time <sup>2</sup>	t <sub>d(off)</sub>	$V_{SS}$ = 12V, $I_S \cong 5A, V_{GS}$ = 4.5V	TBD			
Fall Time <sup>2</sup>	$T_{f0}$	_	TBD			
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T <sub>J</sub> = 25 °C)						
Forward Source-Source Voltage <sup>1</sup>	V <sub>F</sub>	$I_{\rm S}$ = 5A, $V_{\rm GS}$ = 0V	0.6	1.2	V	

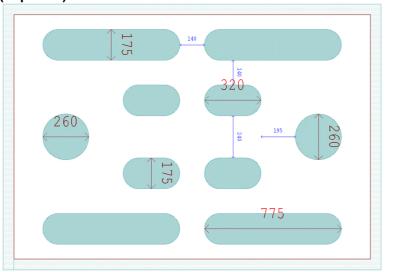
 $^1\text{Pulse test}$  : Pulse Width  $\leq 300~\mu\text{sec},$  Duty Cycle  $\leq 2\%.$ 

<sup>2</sup>Independent of operating temperature.



# Package Dimensions, WLCSP 2.080x1.450

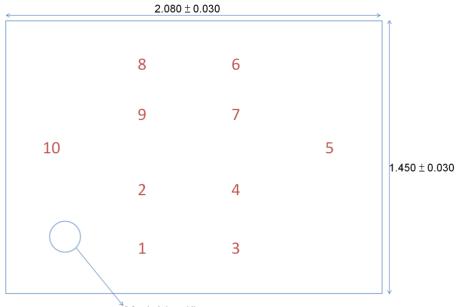




#### (Front View)

0.115 ± 0.0	010
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#### (Bottom View)

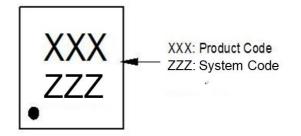


Mark Identifier

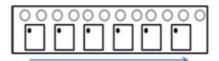
### Note: All Dimension in millimeter

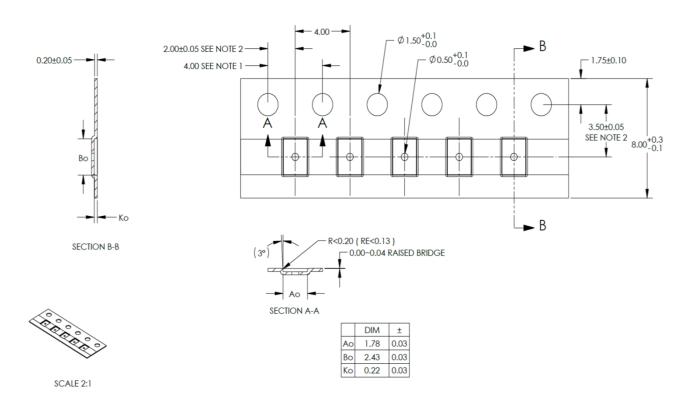


# A. Marking Information(Product Code : A33)



### B. Tape & Reel Information : 5000pcs/Reel





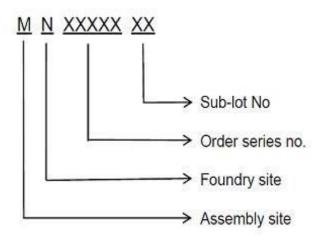
#### Note: All Dimension in millimeter

**UNIKC** Semiconductor Power Module for Battery Pack

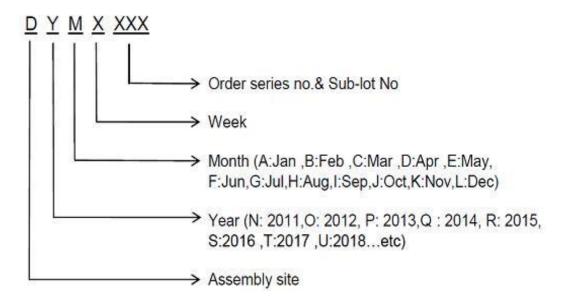


C. Lot No. & Date Code Rule

1.Lot No.



# 2.Date Code



UNIKC

#### Semiconductor

Power Module for Battery Pack



### D. Label rule

#### Label content



1	Label Size	30 * 90 mm		
2	Font style	Times New Roman or Arial (或可区分英文"0"和数字"0","G和"Q"的字型即可)		
3	U-NIKC	Height: 4 mm		
4	Package	Height: 2 mm		
5	Device	Height: 3 mm (Max: 16 Digit)		
6	Lot	Height: 3 mm (Max: 9 Digit) Sub lot		
7	D/C	Height: 3 mm (Max: 7 Digit)		
8	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed		
9	RoHS label	RoHS long axis: 12 mm bottom color: White Font color: Black Font style: Arial		
10	Halogen Free label	G Diameter: 10 mm bottom color: Green   Font color: Black Font style: Arial		
11	Scan information	Device / Lot / D/C / QTY , Insert " / " between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least		



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